# **BUFFER GATE DRIVER INTEGRATED CIRCUIT**

## **Features**

- High peak output current
- Negative turn-off bias
- Separate Ron / Roff resistors
- Low supply current
- Under-voltage lockout
- Full time ON capability
- Low propagation delay time
- Gate clamping when no supply
- Automotive qualified

## **Applications**

- High power inverters
- EV/HEV power trains

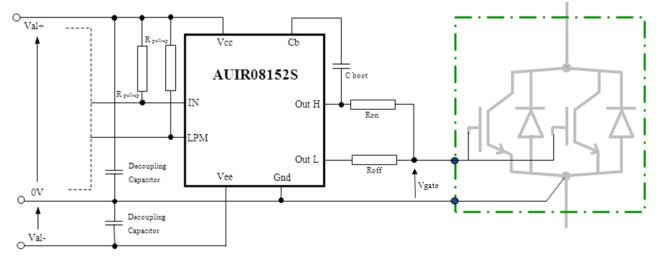
## Description

The AUIR08152 buffer brings high power gate drive capability to all pre-driver stages. It is the output extension of the wide I.R gate driver families. It features a negative Gate bias for applications requiring high levels of dv/dt immunity, a low power consumption mode as well as the full time ON gate drive ability. Shoot-through prevention is extended even when the AUIR08152S supplies are absent by mean of a Gate to Emitter self-clamping impedance.

## Ordering Information

Base Part Number	Package Type	Standard Pack			
Dase Fait Nulliber		Form	Quantity	Complete Part Number	
ALUD004520	SOIC8	Tube	95	AUIR08152S	
AUIR08152S	30100	Tape and reel	2500	AUIR08152STR	

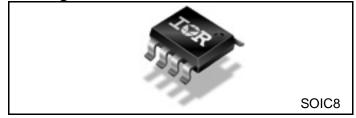
## **Typical Connection**



# Product Summary

Outputs Current:	+/- 10A
Operating Voltage:	13V to 25V
Negative Gate Bias:	0 to -10V

## Package





## **Absolute Maximum Ratings**

Absolute maximum ratings indicate sustained limits beyond which permanent damage to the device may occur. These are stress ratings only, functional operation of the device at these or any other condition beyond those indicated in the "Recommended Operating Condition" is not implied. Exposure to absolute maximum-rated conditions for extended periods may affect device reliability. All voltage parameters are absolute voltages referenced to GND unless otherwise stated in the table. The thermal resistance and power dissipation ratings are measured mounted on board in free air condition.

Symbol	Definition	Min	Max	Units
Vcc-Gnd	Vcc to Gnd maximum voltage	-0.3	+37	
Vcc-Vee	Vcc to Vee maximum voltage	-0.3	+37	
Vcc-VIN	Vcc to Vin maximum voltage	-0.3	+37	V
Vcc-VIpm	Vcc to VLPM maximum voltage	-0.3	+37	
VCB	CB to OUTH max voltage	-0.3	+5.5	
ILPM	LPM pin maximum current	-10	+10	
lin	IN pin maximum current	-10	+10	mA
VOUTH	OUTH pin maximum voltage, DC operation	Vcc - 37	V <sub>CC</sub> + 0.3	V
VOUTL	OUTL pin maximum voltage, DC operation	V <sub>EE</sub> - 0.2	V <sub>CC</sub> + 0.3	
IOUTH	Maximum input transient current to OUTH pin (t < 1us,Ron = $2\Omega$ )		2	٨
IOUTL	Maximum output transient current from OUTL pin (t < 1us, Roff = $2\Omega$ )		1.5	A
PD	Package power dissipation @ $T_A \le 25 \text{ °C}$	_	1 W	
RthJA	Thermal resistance, junction to ambient	_	80	K/W
TJ	Junction temperature	-40	150	
TS	Storage temperature	-55	150	°C
TL	Lead temperature (soldering, 10 seconds)	_	300	

## **Recommended Operating Conditions**

The recommended conditions represent the AUIR08152 optimum performances for the typical application

Symbol	Definition	Min.	Max.	Units
VCC-GND	CC-GND Gate driver positive supply voltage		25	
GND-VEE	Recommended negative gate bias	0	-10	
VCC-VEE	Total supply voltage	15	35	V
VOUTH	OUTH Output voltage	Vcc - 35	Vcc	
VIN,Ipm	IN and LPM pins voltage range	Vcc-35	V <sub>CC</sub>	
Cboot	Recommended bootstrap ceramic capacitor	10	47	
Cload	Maximum recommended equivalent gate capacitor	—	240	nF
Cdec	Recommended Vcc & Vee decoupling capacitors*	22	33 µF	
Ron	OUTH series resistor to gate	1.5	20	
Roff	OUTL series resistor to gate	1.5	20	Ω
R pull-up	Recommended pull-up resistor for IN and LPM pins	tor for IN and LPM pins 10 100		kΩ
PWoff	Minimum recommended OFF time on the IN pin	1		
PWon	Minimum recommended ON time on the IN pin	mmended ON time on the IN pin 1 —		μs

\* Due to the high current application a good quality low ESR capacitor has to be used.

Numbers are indicative, a value about 40 times the load capacitance seen at the OutH and OutL pins is suggested.



## **Static Electrical Characteristics**

Symbol	Definition	Min	Тур	Max	Units	Test Conditions
V <sub>CCUV+</sub>	V <sub>cc</sub> -GND under-voltage rising edge	_	11.7	12.8		
V <sub>CCUV-</sub>	V <sub>CC</sub> -GND under-voltage falling edge	9.6	10.5	—	v	LPM = X, IN = Vcc, Vee = Gnd;
V <sub>ссиун</sub>	V <sub>CC</sub> -GND under-voltage hysteresis	0.5	1.2	_		
VCB <sub>UV (*)</sub>	VCB under-voltage lockout	2.8	4	5.7		
I <sub>QGG</sub>	Current out of the Gnd pin	_	20	60		IN = X, LPM = X
I <sub>QOUTL1</sub>	Current flowing into the OUTL pin	_	0	1.5	μA	IN = Vcc,LPM = X, OUTH = NC, VoutL–Gnd = 15V
I <sub>QEESW</sub>	V <sub>EE</sub> pin current, IN cycling	_	3	8		IN = 10kHz - 50% duty cycle LPM = Vcc, C <sub>LOAD</sub> = 0nF
I <sub>QEE0</sub>	V <sub>EE</sub> pin current – output OFF – normal mode	_	1.5	4		IN = Gnd, LPM = Vcc
I <sub>QEE1</sub>	V <sub>EE</sub> pin current – output ON – normal mode	_	0.8	1.6		IN = Vcc, LPM = Vcc
I <sub>QEELQ0</sub>	V <sub>EE</sub> pin current – output OFF – low power mode		0.6	2.0		IN = Gnd, LPM = Gnd
I <sub>QEELQ1</sub>	$V_{\text{EE}}$ pin current – output ON – low power mode	—	0.8	1.6		IN = Vcc, LPM = Gnd
I <sub>QEEUV</sub>	V <sub>EE</sub> pin current at low Vcc supply	—	0.6	1.6	mA	$IN = X$ , $LPM = X$ , $V_{CC} < V_{CCUV}$ .
I <sub>QB</sub>	CB pin sink current	_	0.5	1		IN = Vcc, LPM = Vcc, Vcb-Vouth = 5.5V
Ιοουτήο	OUTH pin sourced current – normal mode	_	1	3.5		IN = Gnd, LPM = Vcc OUTH = $V_{EE}$ , OUTL = NC
IQOUTHOLQ	OUTH pin sourced current – low power mode	_	0.2	0.5		IN = Gnd, LPM = Gnd OUTH = $V_{EE}$ , OUTL = NC
I <sub>воитн</sub>	CB pin sourced current – normal mode	30	90	_		IN = Gnd, LPM = Vcc, OUTL = NC, CB = OUTH = Vee
I <sub>BOUTH_pl</sub>	CB pin pulsed sourced current – normal mode	90	200	_		Min pulse length 2us guaranteed by design
IBOUTHLQ	CB pin sourced current – low power mode	0.5	5	23		IN = Gnd, LPM = Gnd, OUTL = NC, CB = OUTH = Vee
<sub>DUTH+</sub> /I <sub>OUTL-</sub>	OUTH /OUTL pins output current capability	10	_	_	А	LPM = X VOUTL-: t < 100us, VOUTH+: CB charged
Vcc-VinH	IN pin – output ON voltage	1.5	2.5	_		
Vcc-VinL	IN pin – output OFF voltage	_	4.5	5.5		
V <sub>INhys</sub>	IN pin voltage hysteresis	1	2	_		
Vcc-VLPMH	LPM pin normal mode voltage	1.4	2	_	V	Vcc-Gnd > Vccuv+
Vcc-VLPML	LPM pin low power mode voltage		3.2	3.8		
$V_{\text{LPMhys}}$	LPM pin voltage hysteresis	0.3	1.1	_	]	
I <sub>IN15</sub>	IN pin sourced current	40	90	180		IN = Gnd
I <sub>LPM15</sub>	LPM pin sourced current	10	25	50	μA	LPM = Gnd
	OUTH transistor Rdson	_	100	200		IN = Vcc, lout 10A, t < 100us, Gnd = Vee, Vcв = Vо⊔тн + 5.5V
	OUTL transistor Rdson	_	200	400	mΩ	-IN = Gnd, lout = 10A, t < 100us, Gnd = Vee
IPMOS (*)	OUTH Pulling- up current source	15	30	120	mA	IN = Vcc, LPM = X, Vcc – Vouтн = 1.5v, Vcв – Vouтн = 2.5V

 $V_{CC} - Gnd = 15V, V_{EE-} Gnd = -5V, C_{boot} = 15nF, Ron = Roff = 3\Omega, -40 \text{ }^{\circ}C < T_A < 125 \text{ }^{\circ}C \text{ unless otherwise specified.}$ 

(\*) When VCB – VOUTH < VCB<sub>UV</sub>, OUTH pin remains pulled-up to Vcc (see block diagram).



# **Switching Electrical Characteristics**

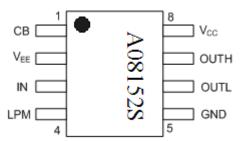
Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions	
t <sub>on</sub>	OUTH turn on propagation delay	1	150	350			
t <sub>off</sub>	OUTL turn off propagation delay		230	350		Saa parametera definitiona	
t <sub>off_VCBuv</sub>	OUTL turn off prop. delay when VcB < VCBuv $^*$	1	90	350		See parameters definitions LPM = X	
tr	OUTH rise time	1	50	150			
t <sub>f</sub>	OUTL fall time	1	50	150	ns		
t <sub>rLQ</sub>	OUTH rise time (IN=1, Vcc ramping up, LPM = Gnd)		50	250		$V_{EE}$ = LPM = Gnd, IN = Vcc	
t <sub>fLQ</sub>	OUTL fall time (IN=1, Vcc ramping down, LPM = Gnd)		50	250		$V_{EE}$ = LPM = Gnd, IN = Vcc	
Min Out-ON	ON time for 0.5µs IN pulse	200	600	900		Cload = open	
Min Out-OFF cb discharged	OFF time for 0.5µs IN pulse, CB discharged	200	500	900		Cload = open, CB = 15 nF	
Min Out-OFF cb charged	OFF time for 0.5µs IN pulse, CB charged	200	400	900		Cload = open, CB = 15 nF	
t <sub>onLPM</sub>	LPM activation time (from LPM edge to ICB < IBOUTH/2) LPM deactivation time (from LPM edge to ICB > IBOUTH/2)		0.6	3		by design	
t <sub>offLPM</sub>			0.6	3	μs	by design	

\* See also Fig. 5

## **Truth Table**

IN	LPM	VCC	OUTH	OUTL	Status
Х	Х	< Vccuv	Open	Vee	IGBT or MOSFET = OFF – Low power mode
Gnd	Gnd	> Vccuv	Open	Vee	IGBT or MOSFET = OFF – Low power mode
Gnd	Vcc	> Vccuv	Open	Vee	IGBT or MOSFET = OFF - Normal mode
Vcc	Gnd	> Vccuv	Vcc	Open	IGBT or MOSFET = ON – Low power mode
Vcc	Vcc	> Vccuv	Vcc	Open	IGBT or MOSFET = ON - Normal mode

## Lead Assignments



## Lead Definitions

Symbol	Description	Pin
СВ	External Bootstrap capacitor (cf. typical connection schematic)	1
Vee	Negative Supply Pin	2
IN	Gate Drive Input, (IN= Vcc forces OutH = high)	3
LPM	Low Power Mode Input, LPM= GND activates the Low Power Mode	4
GND	0V – IGBT Emitter or MOSFET Source Connection (cf. typical connection schematic)	5
OUTL	Gate Drive Output Pull down	6
OUTH	Gate Drive Output Pull up	7



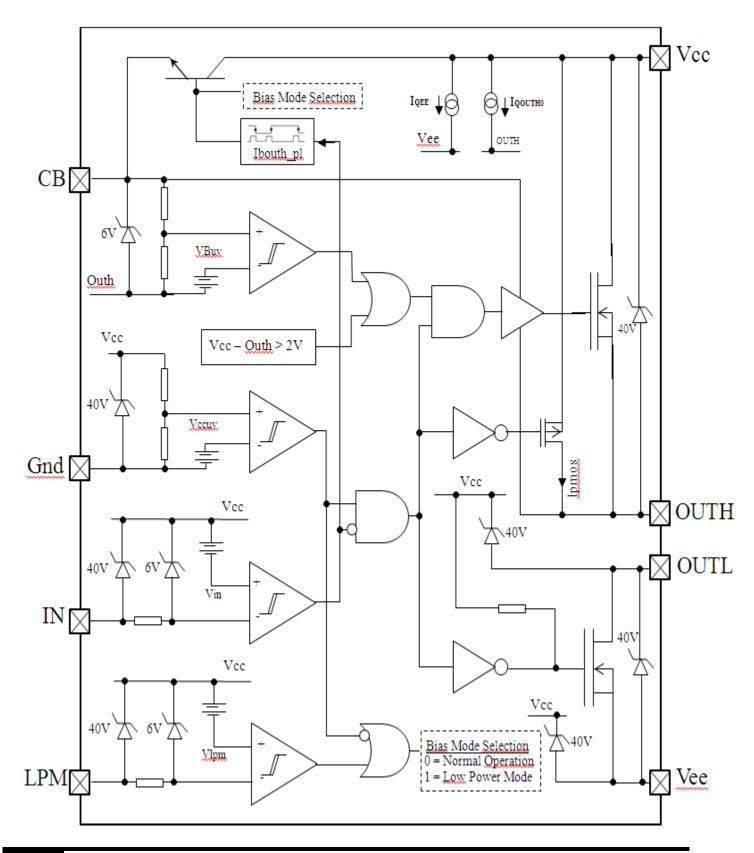
# AUIR08152S

Vcc

Positive Supply Pin

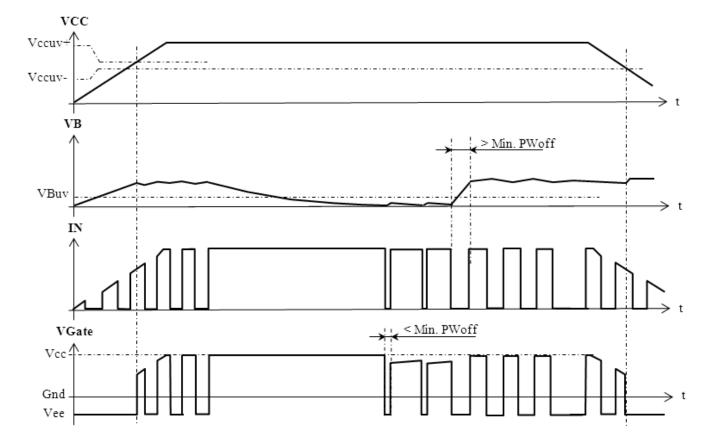


# Functional Block Diagram



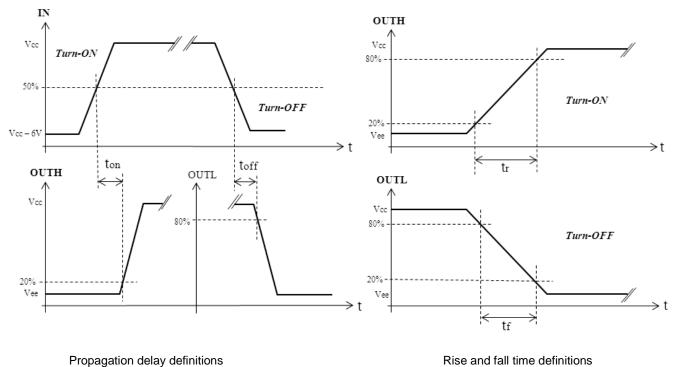


# **Timing Diagram**



# **Parameters Definitions**

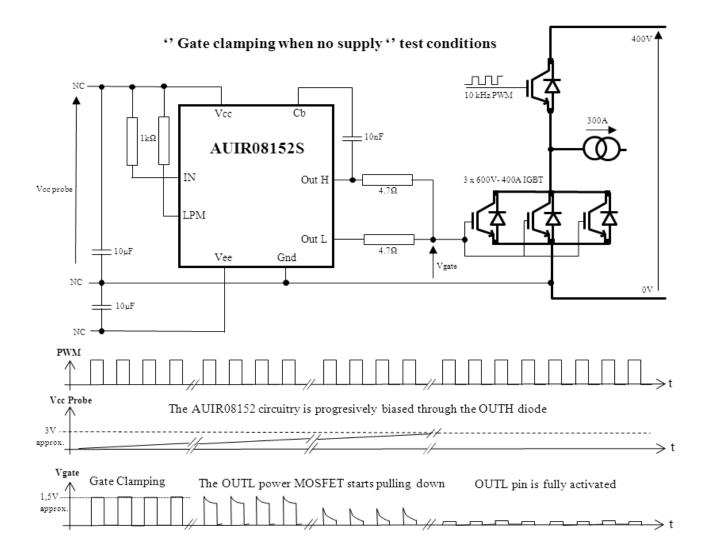


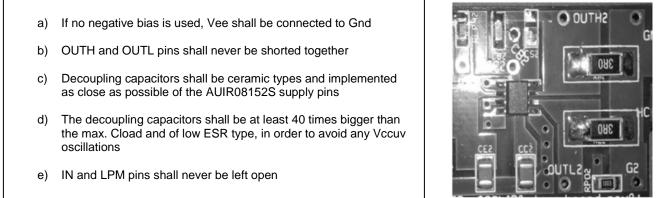


## Application Tips

The AUIR08152S features a self-clamping gate protection in case of the auxiliary power supply disappears. A resistor is pulling up the gate of the OUTL internal power MOSFET to keep OutL pulled down until a minimum Vcc is applied, when Vcc disappears (< about 3V) then the Vgate is clamped via the OUTH ESD diode. In this situation forcing OutL high injects current into the pin that charges the Vcc decoupling capacitor and reactivates the internal OUTL output power MOSFET (for more info see the Functional Block Diagram).







PCB Layout Example

8



## Parameters

Figures are given for typical value @ Tj=25°C otherwise specified

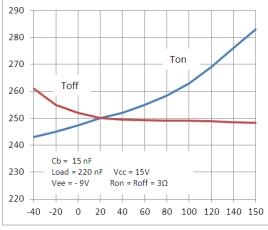


Figure 1: Ton and Toff (ns) Vs Temperature (°C)

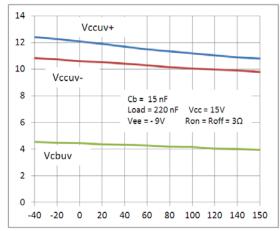
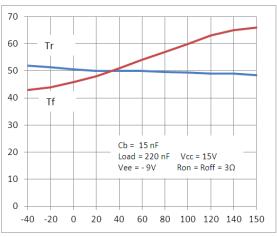


Figure 3: Vccuv+, Vccuv- and Vcbuv (V) Vs Temperature (°C)



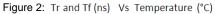




Figure 4: OUTH & OUTL Rdson's Vs Temperature (°C)



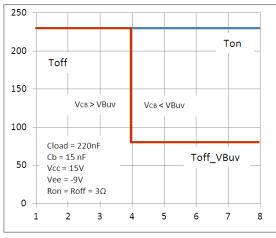


Figure 5: Ton, Toff (ns) Vs IN pulse duration (µs)



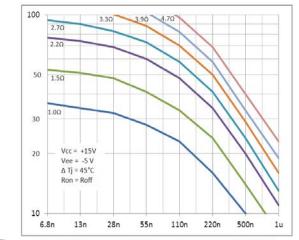
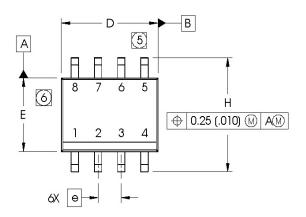
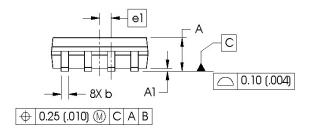


Figure 6: Max PWM Frequency (kHz) Vs Gate Capacitance (F) & Rg ( $\Omega$ )

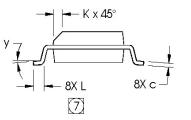


Dimensions are shown in millimeters (inches)



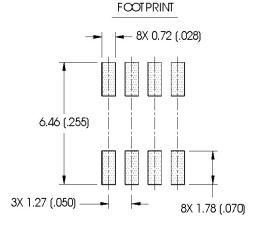


DIM	INC	HES	MILLIN	IETERS	
	MIN MAX		MIN	MAX	
А	.0532	.0688	1.35	1.75	
A1	.0040	.0098	0.10	0.25	
b	.013	.020	0.33	0.51	
С	.0075	.0098	0.19	0.25	
D	.189	.1968	4.80	5.00	
E	.1497	.1574	3.80	4.00	
е	.050 B/	ASIC	1.27 BASIC		
e1	.025 B/	ASIC	0.635 BASIC		
Н	.2284	.2440	5.80	6.20	
К	.0099	.0196	0.25	0.50	
L	.016	.050	0.40	1.27	
У	0°	8°	0°	8°	



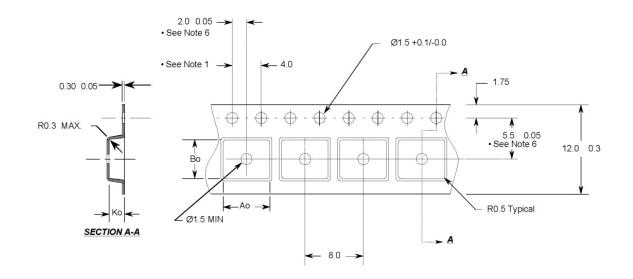
NOTES:

- 1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- 2. CONTROLLING DIMENSION: MILLIMETER
- 3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
- 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- 5 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
- 6 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
- DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.





## Tape & Reel SO8



Ao = 6.4 mm

Bo = 5.2 mm Ko = 2.1 mm

 Notes:
 0.2

 1. 10 sprocket hole pitch cumulative tolerance
 0.2

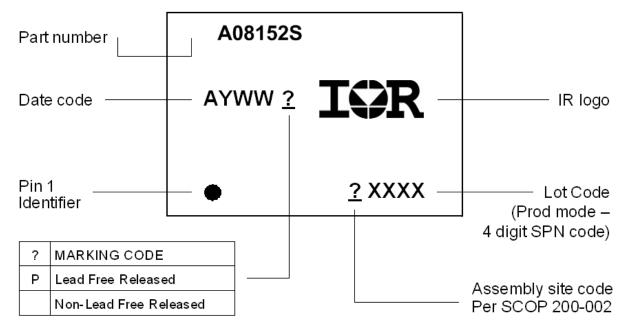
 2. Camber not to exceed 1mm in 100mm
 3. Material: Black Conductive Advantek Polystyrene

- 4. Ao and Bo measured on a plane 0.3mm above the
- bottom of the pocket 5. Ko measured from a plane on the inside bottom of the
- No measured normal plane on the inside bottom of the pocket to the top surface of the carrier.
   Pocket position relative to sprocket hole measured as
- true position of pocket, not pocket hole.

- All Dimensions in Millimeters -



## **Part Marking Information**



# **Qualification Information**<sup>†</sup>

Qualif	ication Level	Automotive (per AEC-Q100) Comments: This family of ICs has passed an Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.		
Moisture Sensitivity Level		SOIC8N	MSL2 <sup>††</sup> 260°C (per IPC/JEDEC J-STD-020)	
	Machine Model	Class M2 (+/-200V) (per AEC-Q100-003)		
ESD	Human Body Model	Class H2 (+/-2500V) (per AEC-Q100-002)		
	Charged Device Model	Class C4 (Pass +/-1000V) (per AEC-Q100-011)		
IC Lat	IC Latch-Up Test		lass II, Level A AEC-Q100-004)	
RoHS	Compliant	Yes		

- + Qualification standards can be found at International Rectifier's web site http://www.irf.com/
- ++ Higher MSL ratings may be available for the specific package types listed here.Please contact your International Rectifier sales representative for further information.



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# **Revision History**

Revision	Date	Notes/Changes
A1	August 5 <sup>th</sup> , 2013	Preliminary Datasheet AUIR08152S
A2	August 23 <sup>rd</sup> 2013	Advanced datasheet
A3	August 26 <sup>th</sup> 2013	Advanced datasheet
A4	September 2 <sup>nd</sup> 2013	Final datasheet, updated lout+ and lout- definition